



TN2907A

PNP General Purpose Amplifier

- This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA.
- Sourced from process 63.



TO-226

1. Collector 2. Base 3. Emitter

Absolute Maximum Ratings* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current - Continuous	800	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	$^\circ\text{C}$

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These rating are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	$^\circ\text{C}/\text{W}$

Electrical Characteristics* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
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Off Characteristics

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	60		V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}, I_E = 0$	5		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 50\text{V}, I_E = 0$ $V_{CB} = 50\text{V}, I_E = 0, T_A = 150^\circ\text{C}$		10 10	nA μA
I_{CEX}	Collector Cut-off Current	$V_{CE} = 30\text{V}, V_{BE} = 0.5\text{V}$		50	nA

On Characteristics

h_{FE}	DC Current Gain	$I_C = 0.1\text{mA}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}^*$	75 100 100 100 50	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150\text{mA}, I_B = 15\text{mA}^*$ $I_C = 500\text{mA}, I_B = 50\text{mA}^*$		0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{mA}, I_B = 15\text{mA}^*$ $I_C = 500\text{mA}, I_B = 50\text{mA}$		1.3 2.6	V V

Small Signal Characteristics

C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 100\text{kHz}$		8.0	pF
C_{ibo}	Input Capacitance	$V_{EB} = 2.0\text{V}, I_C = 0, f = 100\text{kHz}$		30	pF

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle = 2%**NOTES:**

1) All voltages (V) and currents (A) are negative polarity for PNP transistors.



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